A SEMICONDUCTOR WAFER WITH A HETEROEPITAXIAL LAYER AND A METHOD FOR PRODUCING THE WAFER

Abstract:

A semiconductor wafer comprising a substrate having a first side and a second side; a fully or partially relaxed heteroepitaxial layer deposited on the first side of the substrate; and a stress compensating layer deposited on the second side of the substrate. The wafer is produced in a method comprising depositing on a first side of a substrate a fully or partially relaxed heteroepitaxial layer at a deposition temperature; and before cooling the wafer from the deposition temperature, providing a stress compensating layer on a second side of the substrate.

Fig. 2